

N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY							
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)Max.$	I _D (A)	Q _g (Typ.)				
20	$0.300 \text{ at V}_{GS} = 4.5 \text{ V}$	0.9	3.5				
	0.350 at V _{GS} = 2.5 V	0.7	3.5				

FEATURES

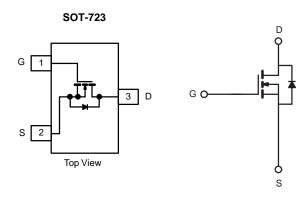
- Halogen-free According to IEC 61249-2-21 Definition
- DefinitionTrench Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

- · Load Switching for Portable Devices
- DC/DC Converter



ABSOLUTE MAXIMUM RATINGS	$(T_A = 25 ^{\circ}C, unlet)$	ess otherwise	noted)		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	20		V
Gate-Source Voltage		V_{GS}	± 12		V
0 11 0 1 (T 150.00)8	T _A = 25 °C	- I _D	0.9	0.72	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		0.68	0.57	
Pulsed Drain Current (t = 300 µs) ^b		I _{DM}	3.5		Α
Continuous Source Current (Diode Conduction) ^a		I _S	0.72	0.6	
D 0: 1 1: 2	T _A = 25 °C	В	0.35	0.28	W
Power Dissipation ^a	T _A = 70 °C	P_{D}	0.21	0.16	VV
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
Manipulation to Applicant	t ≤ 5 s	R _{thJA}	120	145	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		140	175		
Maximum Junction-to-Foot	Steady State	R _{thJF}	62	78		

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.

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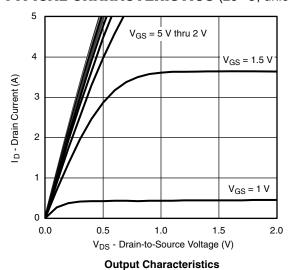
			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			٧	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.50		0.90	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zava Cata Valta aa Dusiin Cuuruut	ı	V _{DS} = 20 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			75	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 4.5 \text{ V}$	6			Α	
	D	$V_{GS} = 4.5 \text{ V}, I_D = 0.9 \text{A}$		0.300		0	
Drain-Source On-Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 0.7 \text{ A}$		0.350		Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 5 \text{ V}, I_D = 0.9 \text{ A}$		13		S	
Diode Forward Voltage	V_{SD}	I _S = 0.95 A, V _{GS} = 0 V		0.7	1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			1.5	1.9		
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 0.9 \text{A}$		0.25		nC	
Gate-Drain Charge	Q _{gd}			0.40			
Gate Resistance	R_{g}	f = 1 MHz	2	4	8	Ω	
Switching							
Turn-On Delay Time	t _{d(on)}			8	15		
Rise Time	t _r	V_{DD} = 10 V, R_L = 2.78 Ω		7	15		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 0.9$ A, $V_{GEN}=4.5$ V, $R_g=1~\Omega$		30	45	ns	
Fall Time	t _f			7	15		
Source-Drain Reverse Recovery Time	t _{rr}	L = 0.0 A dl/dt = 100 A/vo		8.5	15		
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = 0.9 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		2	4	nC	

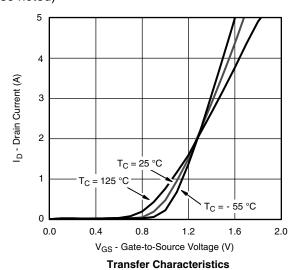
Notes:

- a. Pulse test: Pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

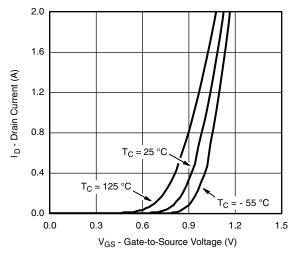
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



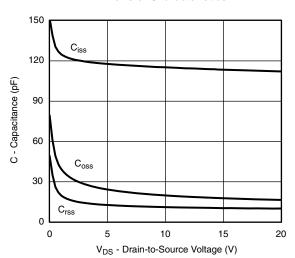




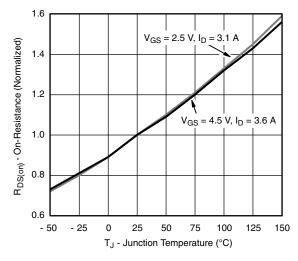
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



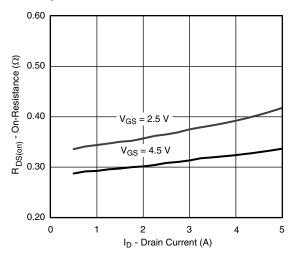
Transfer Characteristics



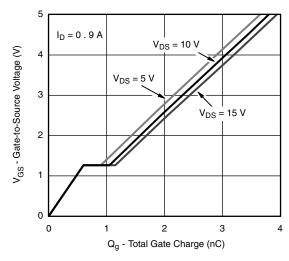
Capacitance



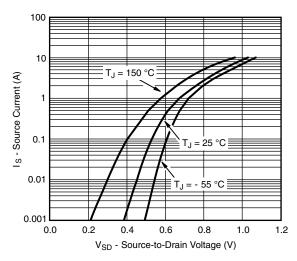
On-Resistance vs. Junction Temperature



On-Resistance vs. Drain Current



Gate Charge

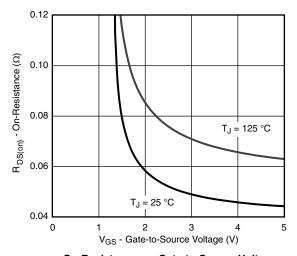


Source-Drain Diode Forward Voltage

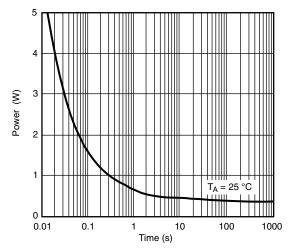
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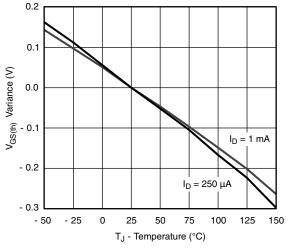
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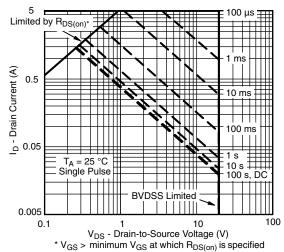
On-Resistance vs. Gate-to-Source Voltage



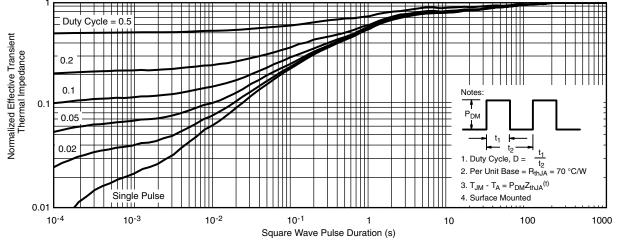
Single Pulse Power







Safe Operating Area, Junction-to-Ambient

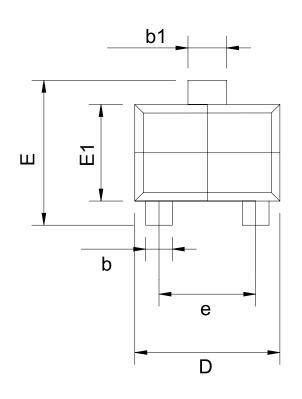


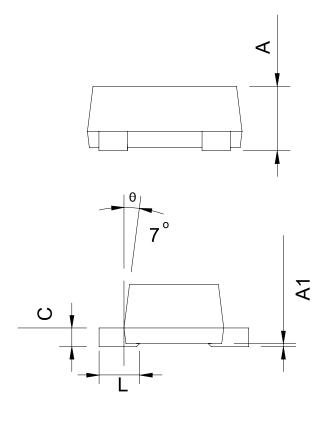
Normalized Thermal Transient Impedance, Junction-to-Ambient

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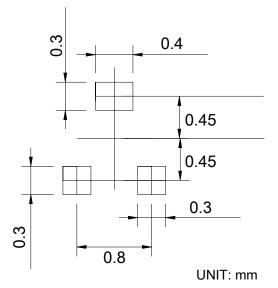
SOT-723: 3 Leads





Ş	SOT-723					
SYMBOL	MILLIM	ETERS	INCHES			
	MIN.	MAX.	MIN.	MAX.		
Α	-	0.500	-	0.020		
A1	0.000	0.050	0.000	0.002		
b	0.170	0.270	0.007	0.011		
b1	0.270	0.370	0.011	0.015		
С	-	0.150	-	0.006		
D	1.150	1.250	0.045	0.049		
Е	1.150	1.250	0.045	0.049		
E1	0.750	0.850	0.030	0.033		
е	0.800	TYP.	0.03	1 TYP.		
L	0.32	BSC	0.013	BSC		
-	°F	REF.	°F	REF.		

RECOMMENDED LAND PATTERN



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